RUTTONSHA

Ruttonsha International Rectifier Ltd.

SILICON RECTIFIERS

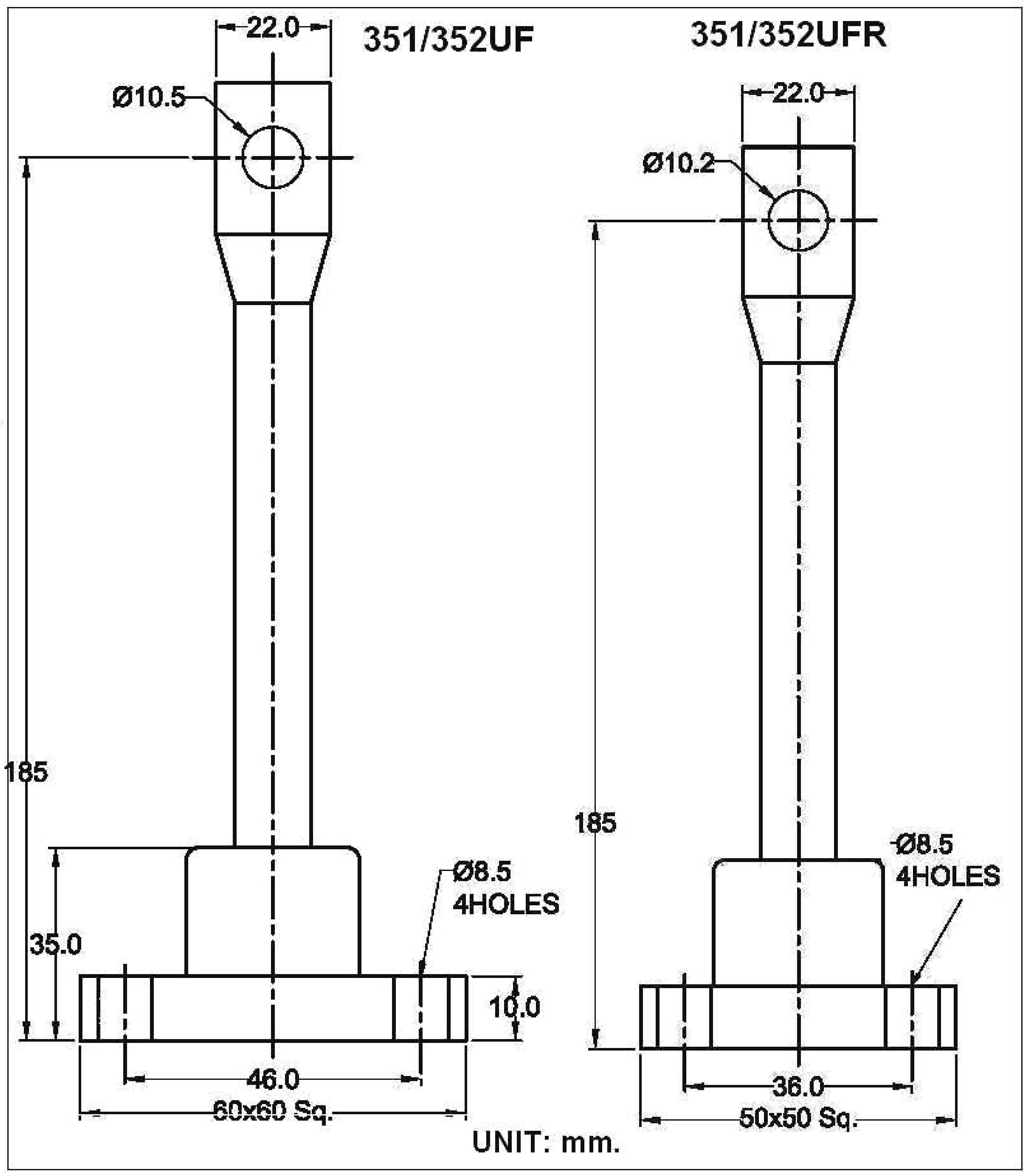
351/352 Ampere Silicon Power Diodes

FEATURES

- *Diffused series.*
- *Available in reverse and normal polarity.*
- *Device conforms to IS 3700 (III) & IS 4400 (III).*

ELECTRICAL SPECIFICATIONS

$I_{F(AV)}$	Maximum average forward current $T_c = 125^0$C	351/352A
V_{FM}	Maximum peak forward voltage drop @ Rated I_F = 1050A (Peak)	1.20 V
I_{FSM}	Maximum peak one cycle (non-rep.) surge current 10 msec.	6000 A
I_{FRM}	Maximum repetitive peak forward current	1100 A
I^2t	Max. I^2t rating (non-rep.) for 5 to 10 msec.	180 KA^2Sec
$V_{F(TO)}$	Max, value of threshold voltage	0.86 V
rf	Max, value of forward slop resistance	0.15 mΩ



THERMAL MECHANICAL SPECIFICATIONS

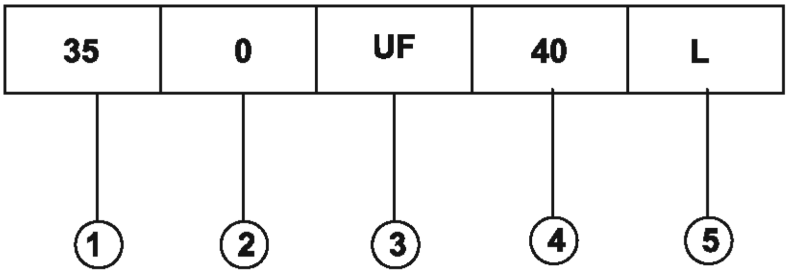
θ_{J-C}	Maximum thermal resistance junction to case	351/352 UF 0.15^0 C/W 351/352 UFR 0.02^0 C/W
θ_{C-H}	Contact thermal resistance	0.02^0 C/W
T_J	Operating junction temp.	-65^0C to 175^0C
T_{stg}	Storage temperature	-65^0C to 200^0C
	Mounting torque	0.7 M-Kg min 0.86 M-Kg max.
W	Approx. weight	330 gms.

ELECTRICAL RATINGS

TYPE	NUMBER 351/352 UF/UFR	40	60	80	100	120	140	160
V_{RRM}	Max. repetitive peak reverse voltage (V)	400	600	800	1000	1200	1400	1600
V_{RSM}	Max. non-repetitive peak reverse voltage (V)	500	700	900	1100	1300	1500	1700
$V_{R(RMS)}$	Max. R.M.S. reverse voltage (V)	280	420	560	700	840	980	1120
V_R	Max. D.C. Blocking voltage (V)	400	600	800	1000	1200	1400	1600
	Recommended R.M.S. working voltage (V)	160	240	320	400	480	560	640
I_{RM}	Max. Average reverse leakage current @ V_{RRM} T_C (mA)	20	20	20	20	20	20	20

SILICON RECTIFIERS

ORDER INFORMATION TABLE



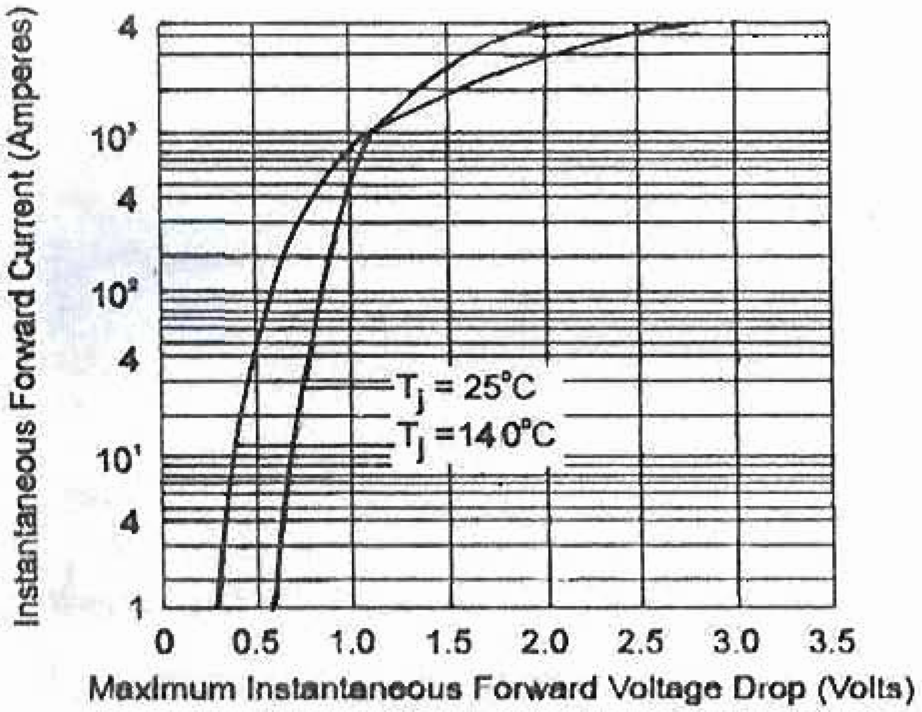
① - 35 - Essential Part no.

② - 0 - Round Flat Base
1 - 50 x 50 Square Flat Base
2 - 60 x 60 Square Flat Base

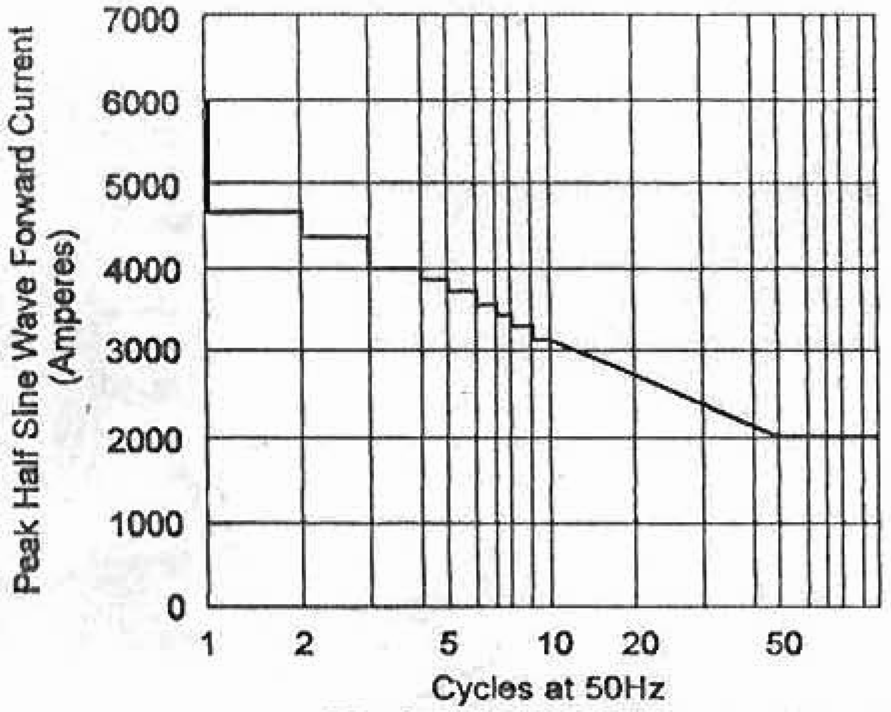
③ - UF - Normal polarity
UFR - Reverse polarity

④ - Voltage Rating (See table)

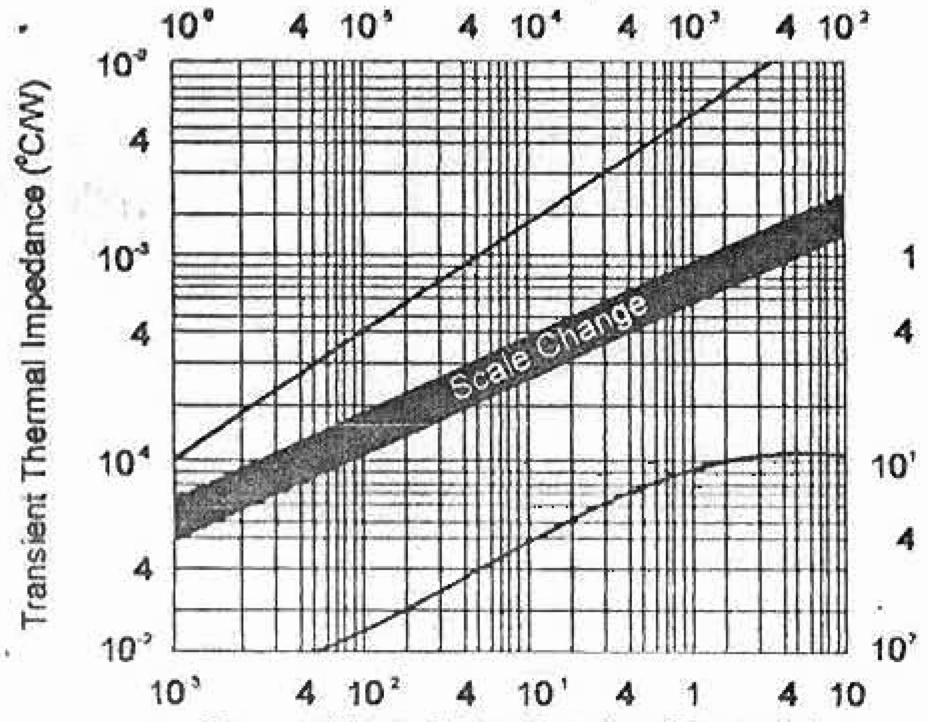
⑤ - None - Without 'L' bracket
L - With 'L' bracket



Forward Voltage Drop Vs. Forward Current



Maximum Non Recurrent Surge Current



Transient Thermal Impedance